New Jersey Semi-Conductor Products, Inc.

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Silicon NPN Power Transistor — 2N6360

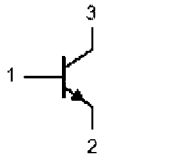
DESCRIPTION

- Excellent Safe Operating Area
- High DC Current Gain-
  : h_{FE}=15-60(Min)@I_C = 6A
- Low Saturation Voltage-
  : $V_{CE(sat)}$= 1.4V(Max)@ I_C = 6A

APPLICATIONS

- Designed for high power applications and switching circuits such as relay or solenoid drivers, DC-DC converters or Inverters.





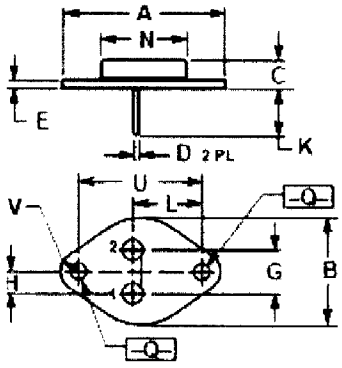
PIN
1. BASE
2. EMITTER
3. COLLECTOR (CASE)
TO-3 package

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	12	A
I_{CM}	Collector Current-Peak	24	A
I_B	Base Current-Continuous	4	A
P_C	Collector Power Dissipation @T_C=25℃	150	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.17	℃/W



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 200mA; I_B= 0	100		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 6A; I_B= 0.6A		1.4	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 12A; I_B= 2.4A		4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 6A; V_{CE}= 4V		2.2	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 100V; I_B= 0		2.0	mA
I_{CEX}	Collector Cutoff Current	V_{CE}= 120V; $V_{BE(off)}$= 1.5V V_{CE}= 120V; $V_{BE(off)}$= 1.5V, T_C=150℃		2.0 10	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7V; I_C=0		5.0	mA
h_{FE-1}	DC Current Gain	I_C= 6A; V_{CE}= 4V	15	60	
h_{FE-2}	DC Current Gain	I_C= 12A ; V_{CE}= 4V	5		
f_T	Current-Gain—Bandwidth Product	I_C= 1A; V_{CE}= 4V	0.2		MHz

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